

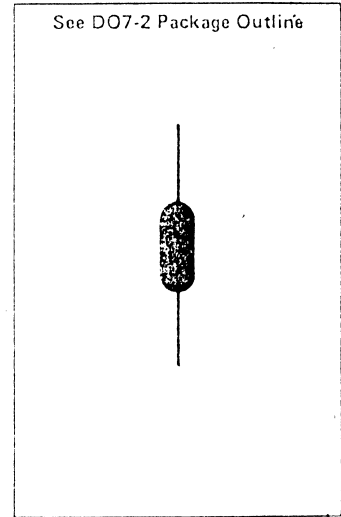
1N459 • 1N459A

LOW LEAKAGE
 DIFFUSED SILICON PLANAR* DIODES

- BV . . . 200 V (MIN) @ 100 μ A
- I_R . . . 25 nA (MAX) @ 175 V

ABSOLUTE MAXIMUM RATINGS (Note 1)

Maximum Temperatures		
Storage Temperature		-65°C to +200°C
Operating Temperature		175°C
Maximum Power Dissipation		
Total Dissipation at 25°C Ambient Temperature		400 W
Maximum Voltages and Currents		
WIV Working Inverse Voltage		175 V
I _O Average Rectified Current		40 mA
I _F Forward Current Steady State DC		100 mA
i _f Recurrent Peak Forward Current		125 mA
i _f (surge) Peak Forward Surge Current		500 mA
	Pulse Width = 1.0 s	2.0 A
	Pulse Width = 1.0 μ s	



ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC	1N459		1N459A		UNITS	TEST CONDITIONS
		MIN.	MAX.	MIN.	MAX.		
V _F	Forward Voltage		1.0		1.0	V	I _F = 3.0 mA
I _R	Reverse Current		25		25	nA	I _F = 100 mA
			5.0		5.0	μ A	V _R = 175 V, T _A = 150°C
BV	Breakdown Voltage	200		200		V	I _R = 100 μ A
C	Capacitance (Note 2)		6.0			pF	V _R = 0, f = 1.0 MHz

